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FR101 THRU FR107

Features

- Low Cost
- Low Leakage
- Low Forward Voltage Drop
- High Current Capability
- Fast Switching Speed For High Efficiency

1 Amp Silicon Rectifier 50 to 1000 Volts

Maximum Ratings

- Operating Temperature: -55°C to +150°C
- Storage Temperature: -55°C to +150°C

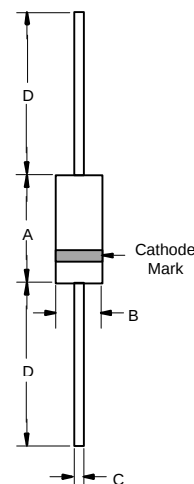
Catalog Number	Device	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
FR101	---	50V	35V	50V
FR102	---	100V	70V	100V
FR103	---	200V	40V	200V
FR104	BA157	400V	280V	400V
FR105	BA158	600V	420V	600V
FR106	---	800V	560V	800V
FR107	BA159	1000V	700V	1000V

Electrical Characteristics @ 25°C Unless Otherwise Specified

Average Forward Current	$I_{F(AV)}$	1 A	$T_A = 55^\circ\text{C}$
Peak Forward Surge Current	I_{FSM}	30A	8.3ms, half sine
Maximum Instantaneous Forward Voltage	V_F	1.3V	$I_{FM} = 1.0\text{A};$ $T_A = 25^\circ\text{C}$
Maximum DC Reverse Current At Rated DC Blocking Voltage	I_R	5.0 μA 100 μA	$T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$
Maximum Reverse Recovery Time FR101-104 FR105 FR106-107	T_{rr}	150ns 250ns 500ns	$I_F=0.5\text{A}, I_R=1.0\text{A},$ $I_{rr}=0.25\text{A}$
Typical Junction Capacitance	C_J	15pF	Measured at 1.0MHz, $V_R=4.0\text{V}$

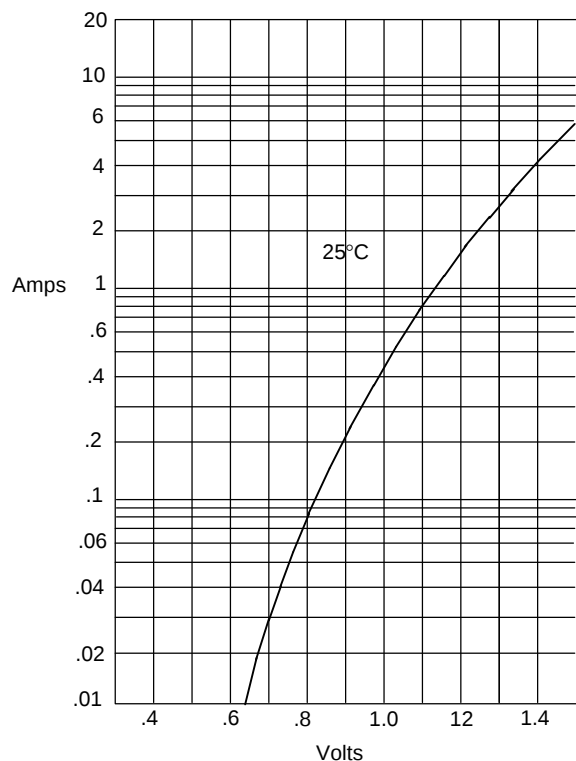
*Pulse Test: Pulse Width 300 μsec , Duty Cycle 1%

DO-41



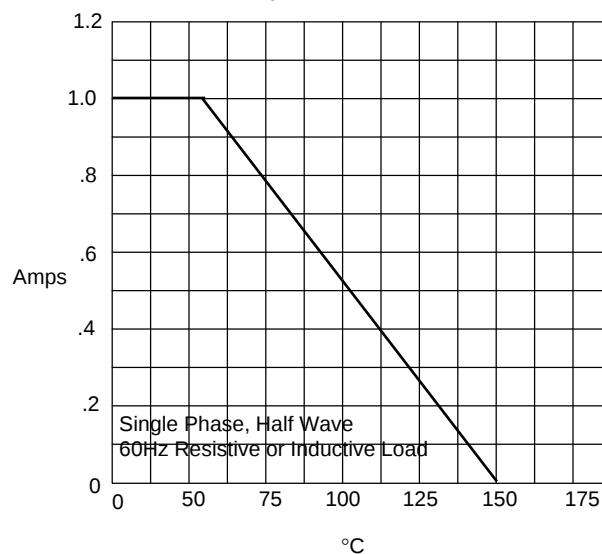
DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.166	.205	4.10	5.20	
B	.080	.107	2.00	2.70	
C	.028	.034	.70	.90	
D	1.000	---	25.40	---	

Figure 1
Typical Forward Characteristics



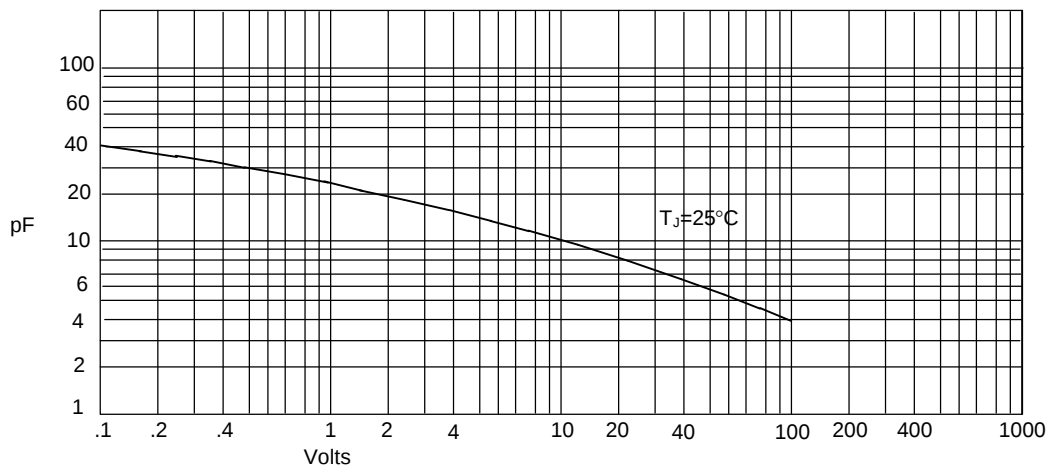
Instantaneous Forward Current - Amperes versus
Instantaneous Forward Voltage - Volts

Figure 2
Forward Derating Curve



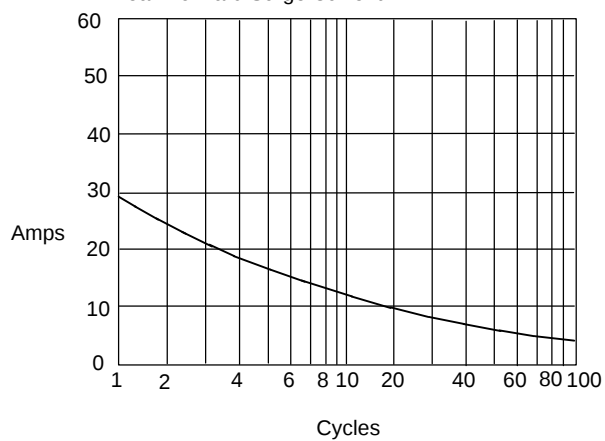
Average Forward Rectified Current - Amperes versus
Ambient Temperature - °C

Figure 3
Junction Capacitance



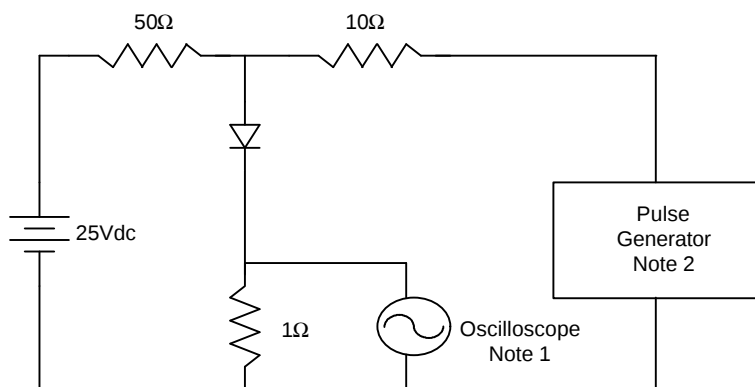
Junction Capacitance - pF versus
Reverse Voltage - Volts

Figure 4
Peak Forward Surge Current



Peak Forward Surge Current - Amperes *versus*
Number Of Cycles At 60Hz - Cycles

Figure 5
Reverse Recovery Time Characteristic And Test Circuit Diagram



Notes:

1. Rise Time = 7ns max.
Input impedance = 1 megohm, 22pF
2. Rise Time = 10ns max.
Source impedance = 50 ohms
3. Resistors are non-inductive

